

REMARKS

This application has been reviewed in light of the Office Action dated September 5, 2006. Claims 1-10 are presented for examination, of which Claim 1 is in independent form. Claim 1 has been amended to clarify the scope of Applicants' invention. Claims 3-10 have been amended narrow claim dependency to Claim 1. Favorable reconsideration is requested.

An Information Disclosure Statement is being filed concurrently herewith.

Claims 4-10 have been objected to under 37 C.F.R. 1.75(c) as being in improper form on the ground that a multiple dependent claim cannot depend from any other multiple dependent claim. It appears based on this rejection that the Examiner failed to consider the June 10, 2005 Preliminary Amendment (the filing of which is evidenced by its identification in the PAIR system) in which the claims were amended to correct any improper multiple dependencies. In addition, Applicants have further amended Claims 4-10 so that they depend only from Claim 1. Applicants respectfully request withdrawal of this objection.

Applicants thank the Examiner for allowing Claims 1-3, and submit the following comments on the reasons for allowance. Claim 1 is directed to a solid state image pickup apparatus including a photodetecting device and one or more thin film transistors connected to the photodetecting device formed in one pixel, wherein a part of the photodetecting device is formed over at least a part of the thin film transistor. The thin film transistor comprises a source electrode, a drain electrode, a first gate electrode, and a second gate electrode arranged on the side opposite to said first gate electrode with respect to the source electrode and the drain electrode, and the first gate electrode and the second gate electrode are connected to a common

gate wiring.

By virtue of the structure recited in Claim 1, the following technical advantages are provided: (1) transferring efficiency of the thin film transistor is improved; and (2) undesirable variation of a threshold voltage of the thin film transistor due to a voltage change of a lower electrode of the photodetecting device is reduced. None of U.S. Patent Application Publication No. 2002/0084419 (Choo), U.S. Patent Application Publication No. 2003/0226974 (Nomura) or U.S. Patent Application Publication No. 2005/0179964 (Izumi) disclose or suggest the structure recited in Claim 1.

In view of the foregoing amendments and remarks, Applicants respectfully request favorable reconsideration and early passage to issue of the present application.

Applicants' undersigned attorney may be reached in our New York office by telephone at (212) 218-2100. All correspondence should continue to be directed to our below listed address.

Respectfully submitted,

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